**Product data sheet** 

## 1. General description

PNP low  $V_{CEsat}$  transistor and NPN Resistor-Equipped Transistor (RET) in one very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

### 2. Features and benefits

- Low V<sub>CEsat</sub> transistor and resistor-equipped transistor in one package
- Low threshold voltage (<1 V) compared to MOSFET</li>
- · Low drive power required
- · Space-saving solution
- · Reduction of component count
- AEC-Q101 qualified

# 3. Applications

- Supply line switches
- Battery charger switches
- · High-side switches for LEDs, drivers and backlights
- · Portable equipment

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
TR1: PNP I	ow V <sub>CEsat</sub> transistor			<u> </u>	<b> </b>	
$V_{CEO}$	collector-emitter voltage	open base	-	-	-40	V
I <sub>Clim</sub>	limiting collector current		-	-	-500	mA
R <sub>CEsat</sub>	saturation resistance	$I_C$ = -500 mA; $I_B$ = -50 mA; $T_{amb}$ = 25 °C; pulsed; $t_p$ ≤ 300 μs; $\delta_{factor}$ ≤ 0.02	-	440	700	mΩ
TR2: NPN r	esistor-equipped transistor	•			'	
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



40 V PNP loadswitch transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		C1 I2 GND2
2	B1	base TR1	□6 □5 □4	
3	O2	output (collector) TR2		R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	H <sub>1</sub> H <sub>2</sub> H <sub>3</sub>	TR1
6	C1	collector TR1	TSSOP6 (SOT363)	E1 B1 O2 sym036

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PBLS4002Y		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>			

### 7. Marking

### Table 4. Marking codes

Type number	Marking code[1]
PBLS4002Y	S2%

[1] % = placeholder for manufacturing site code

40 V PNP loadswitch transistor

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
TR1: PNP I	ow V <sub>CEsat</sub> transistor					
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-40	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>Clim</sub>	limiting collector current			-	-500	mA
I <sub>CM</sub>	peak collector current	t <sub>p</sub> ≤ 1 ms; single pulse		-	-1	mA
I <sub>B</sub>	base current			-	-50	mA
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	200	mW
TR2: NPN r	esistor-equipped transistor		·	·		·
$V_{CBO}$	collector-base voltage	open emitter		-	50	V
$V_{CEO}$	collector-emitter voltage	open base		-	50	V
$V_{EBO}$	emitter-base voltage	open collector		-	10	V
V <sub>I</sub>	input voltage	input voltage TR2 positive		-	30	V
		input voltage TR2 negative		-	-10	V
Io	output current			-	100	mA
I <sub>CM</sub>	peak collector current	t <sub>p</sub> ≤ 1 ms; single pulse		-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	200	mW
Per device						
P <sub>tot</sub>	total power dissipation			-	300	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device							
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### **40 V PNP loadswitch transistor**

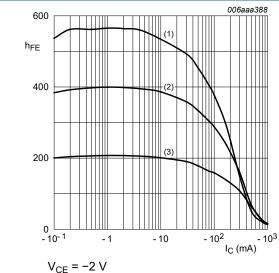
# 10. Characteristics

#### Table 7. Characteristics

Table 7. Cha Symbol	Parameter	Conditions	Min	Тур	Max	Unit
TR1: PNP Io	ow V <sub>CEsat</sub> transistor		l			
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	I <sub>C</sub> = -100 μA; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-40	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-40	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage	$I_C = 0 \text{ A}; I_E = 100 \mu\text{A}; T_{amb} = 25 \text{ °C}$	-6	-	-	V
Ісво	collector-base cut-off	V <sub>CB</sub> = -40 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -40 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 150 °C	-	-	-50	μΑ
I <sub>ЕВО</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -10 mA; pulsed; $T_{amb}$ = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	150	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	40	-	-	
V <sub>CEsat</sub>	collector-emitter	$I_C$ = -10 mA; $I_B$ = -0.5 mA; $T_{amb}$ = 25 °C	-	-	-50	mV
	saturation voltage	$I_C$ = -100 mA; $I_B$ = -5 mA; $T_{amb}$ = 25 °C	-	-	-130	mV
		$I_C$ = -200 mA; $I_B$ = -10 mA; $T_{amb}$ = 25 °C	-	-	-200	mV
		$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02 %; $T_{amb}$ = 25 °C	-	-	-350	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -500 mA; $I_{B}$ = -50 mA; $T_{amb}$ = 25 °C; pulsed; $t_{p}$ ≤ 300 µs;	-	440	700	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$\delta_{\text{factor}} \le 0.02$	-	-	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; $T_{amb}$ = 25 °C; pulsed; $t_p \le 300 \ \mu s; \ \delta_{factor} \le 0.02$	-	-	-1.1	V
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	10	pF
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	100	300	-	MHz
TR2: NPN re	esistor-equipped transisto	r				
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = 100 \ \mu\text{A}; \ I_E = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C}$	50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C	50	-	-	V
СВО	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
CEO	collector-emitter cut-off	V <sub>CE</sub> = 50 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	1	μΑ
	current	V <sub>CE</sub> = 50 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 150 °C	-	-	50	μΑ
Гево	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	900	μΑ
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C	30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-	150	mV

#### 40 V PNP loadswitch transistor

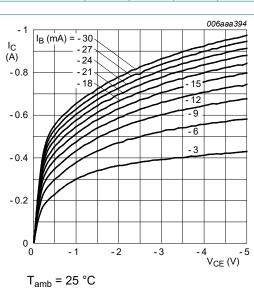
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C	-	1.1	0.5	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	2.5	1.9	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C	-	-	2.5	pF



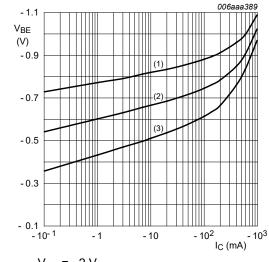
(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \,^{\circ}C$$
  
(3)  $T_{amb} = -55 \,^{\circ}C$ 

TR1 (PNP): DC current gain as a function of Fig. 1. collector current; typical values



TR1 (PNP): Collector current as a function of Fig. 2. collector-emitter voltage; typical values



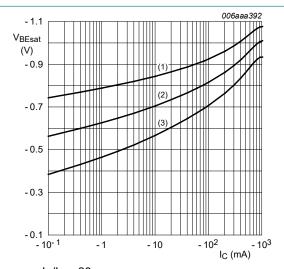
 $V_{CE} = -2 V$ 

$$(1) T_{amb} = -55 °C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 3. TR1 (PNP): Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 20$$

$$(1) T_{amb} = -55 °C$$

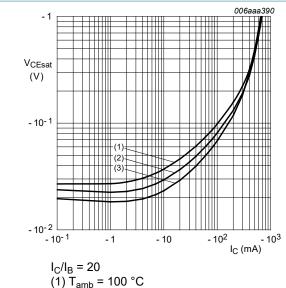
(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 4. TR1 (PNP): Base-emitter saturation voltage as a function of collector current; typical values

 $<sup>(1)</sup> T_{amb} = 100 °C$ 

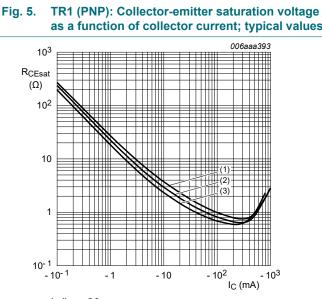
### 40 V PNP loadswitch transistor



$$(1) T_{amb} = 20 °C$$
  
 $(2) T_{amb} = 25 °C$   
 $(3) T_{amb} = -55 °C$ 

(3) 
$$T_{amb} = -55 \,^{\circ}\text{C}$$

as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- 10<sup>- 1</sup>

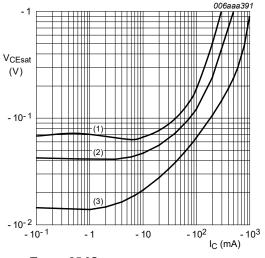
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$$(3) T_{amb} = -55 °C$$

Fig. 7. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values

- 10

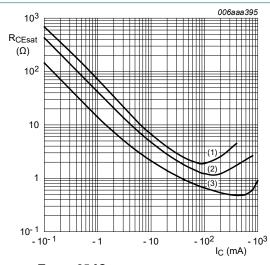
- 10<sup>2</sup>



$$T_{amb} = 25 \,^{\circ}C$$
  
(1)  $I_C/I_B = 100$ 

(2) 
$$I_C/I_B = 50$$
  
(3)  $I_C/I_B = 10$ 

Fig. 6. TR1 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



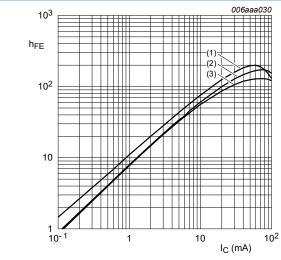
$$T_{amb} = 25 \, ^{\circ}C$$
  
(1)  $I_{C}/I_{B} = 100$ 

(2) 
$$I_C/I_B = 50$$

(3)  $I_C/I_B = 10$ 

Fig. 8. TR1 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values

### 40 V PNP loadswitch transistor

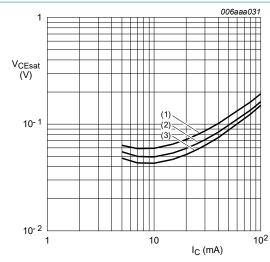


$$V_{CE} = 5 V$$

$$(1) T_{amb} = 150 ° ($$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

TR2 (NPN): DC current gain as a function of Fig. 9. collector current; typical values



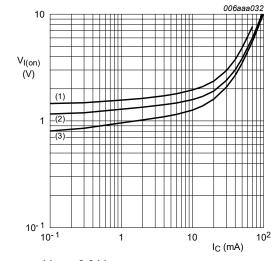
$$I_{\rm C}/I_{\rm B} = 20$$

$$(1) T_{amb} = 100 ° ($$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$I_{C}/I_{B} = 20$$
(1)  $T_{amb} = 100 \, ^{\circ}C$ 
(2)  $T_{amb} = 25 \, ^{\circ}C$ 
(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 10. TR2 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



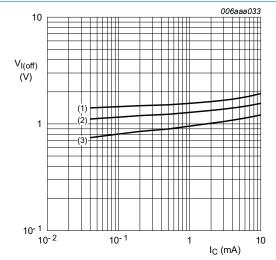
$$V_{CE}$$
 = 0.3  $V$ 

$$(1) T_{amb} = -40 °C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 100 °C$$

of collector current; typical values



$$V_{CE}$$
 = 5  $V$ 

$$(1) T_{amb} = -40 °C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 11. TR2 (NPN): On-state input voltage as a function | Fig. 12. TR2 (NPN): Off-state input voltage as a function of collector current; typical values

40 V PNP loadswitch transistor

### 11. Test information

### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

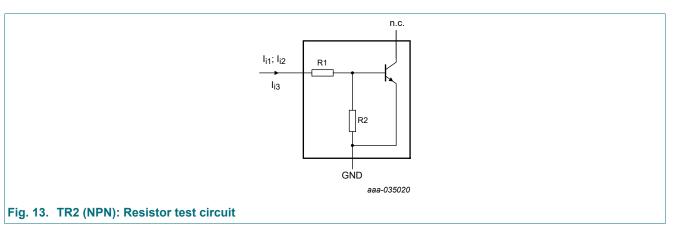
### **Resistor calculation**

Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I_{i2}) - V(I_{i1})}{I_{i2} - I_{i1}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I_{i3})}{R1 \times I_{i3}} - 1$$



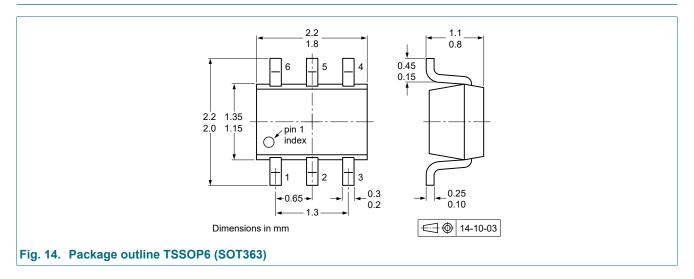
### **Resistor test conditions**

**Table 8. Resistor test conditions** 

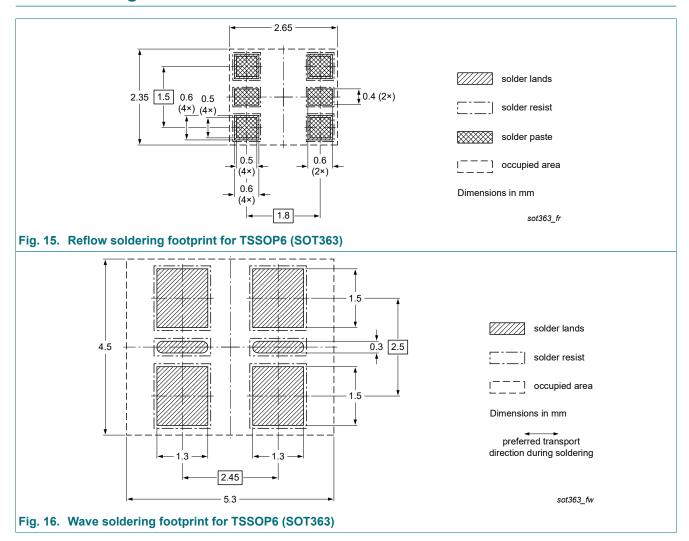
R1 (kΩ)	R2 (kΩ)	Test conditions					
		I <sub>i1</sub>	I <sub>i2</sub>	I <sub>i3</sub>			
Per transistor, for the PNP with negative polarity							
4.7	4.7	750 μΑ	950 μΑ	850 μΑ			

### 40 V PNP loadswitch transistor

# 12. Package outline



### 13. Soldering



### **40 V PNP loadswitch transistor**

# 14. Revision history

### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change	Supersedes		
Data Sileet ID	Release uate	Data sileet status	notice	Superseues		
PBLS4002Y v.4	20220427	Product data sheet	-	PBLS4002Y_PBLS4002V_3		
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Family data sheet splitted to single type data sheets.</li> <li>Packing section removed.</li> </ul>					
PBLS4002Y_PBLS4002V_3	20090212	Product data sheet	-	PBLS4002Y_PBLS4002V_2		
PBLS4002Y_PBLS4002V_2	20050719	Product data sheet	-	PBLS4002Y_PBLS4002V_1		
PBLS4002Y_PBLS4002V_1	20041206	Product data sheet	-	-		

#### 40 V PNP loadswitch transistor

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <a href="https://www.nexperia.com">https://www.nexperia.com</a>.

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PBLS4002Y

### **40 V PNP loadswitch transistor**

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	. Legal information	

For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 27 April 2022

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